



FEATURES

- Circular Active Area
- Ideal for Electron Detection
- 100% Internal QE
- TO-8 Package

Electro-Optical Characteristics at 25°C

Parameters	Test Conditions	Min	Typ	Max	Units
Active Area ¹	Φ 4.9 mm		19		mm ²
Responsivity	(see graph next page)				A/W
Reverse Breakdown Voltage, V _R	I _R = 1 μA		20		Volts
Capacitance, C	V _R = 0 V		1.2	1.5	nF
Rise Time	RL = 50 Ω, V _R = 0 V			1	us
Shunt Resistance	V = ±10 mV	50	100		MOhms
Dark Current	V _R = 13 V			30	nA

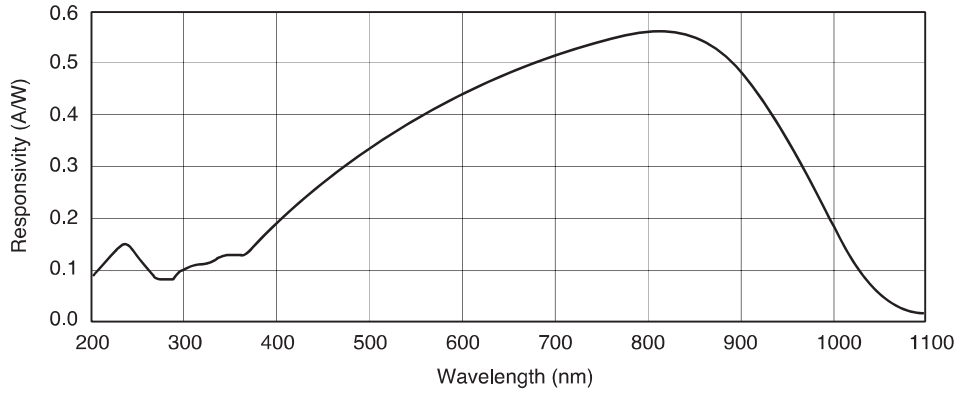
¹ Die active area = Φ5.5 mm, aperture size = Φ4.9 mm.

Thermal Parameters

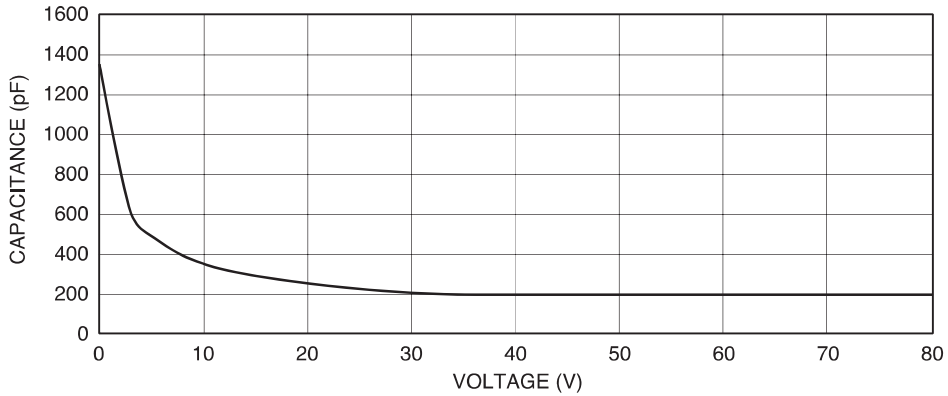
Storage and Operating Temperature Range	Units
Storage Temperature Range	-20°C to 100°C
Operating Temperature Range	20°C to 80°C
Lead Soldering Temperature ¹	240°C



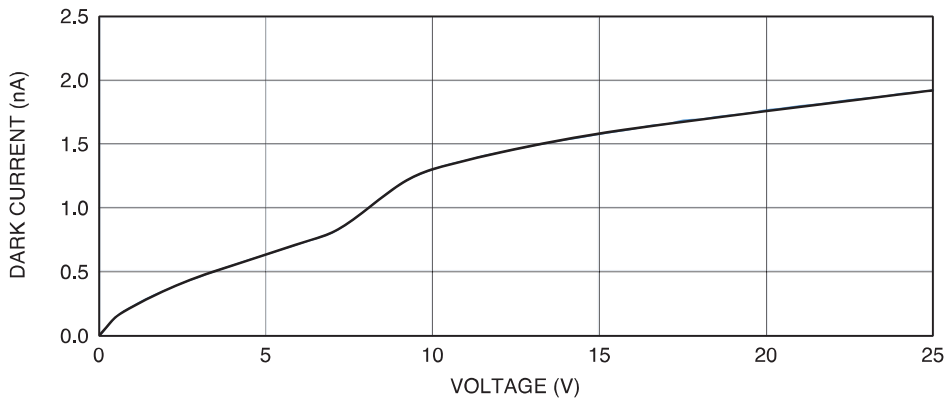
Typical Photon Responsivity



Capacitance vs. Voltage

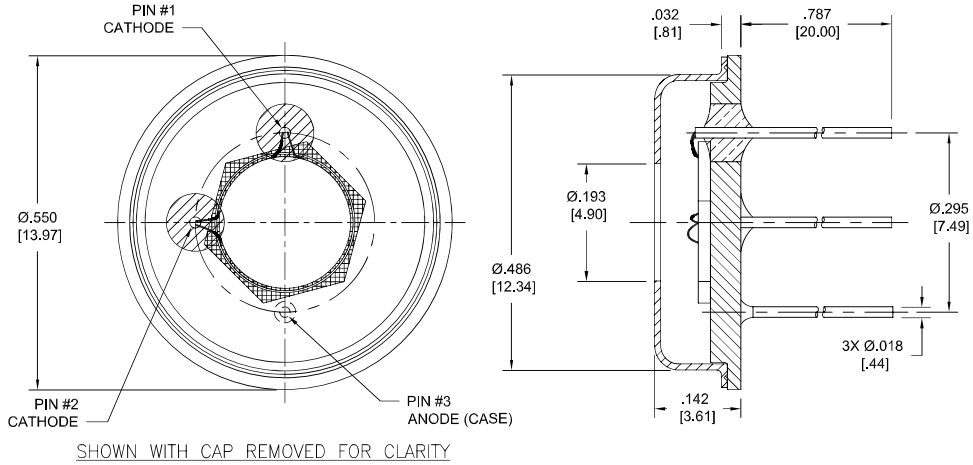


Dark Current vs. Voltage





Package Information



Dimensions are in inch [metric] units.

Specifications are subject to change without prior notice.